

Small Signal Schottky Barrier Diode

**Features**

1. High reliability
2. Low reverse current and low forward voltage
3. High temperature soldering guaranteed  
250 °C/10 seconds, 0.375 (9.5mm) length,  
5 lbs. (2.3kg) tension

**Mechanical Data**

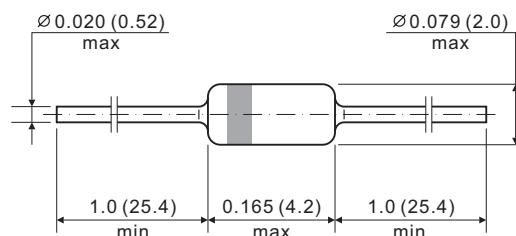
Case: DO-35 Glass Case

Terminals: Plated axial leads, solderable per  
MIL-STD-750, Method 2026

Polarity: Colour band denotes cathode end

Mounting Position: Any

Weight: approx. 0.005 ounce, 0.14grams

**Standard Glass Case JEDEC DO-35***Dimensions in inches and (mm)***Absolute Maximum Ratings** Tamb =25 °C unless otherwise specified

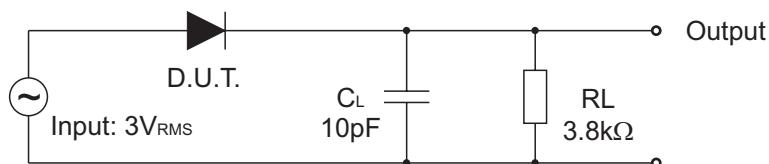
Parameter	Test Condition	Part	Symbol	Value	Unit
Repetitive peak revers voltage		1N60	V <sub>RRM</sub>	40	V
		1N60P	V <sub>RRM</sub>	45	V
Peak forward surge current	T <sub>p</sub> = 1 s	1N60	I <sub>FSM</sub>	150	mA
		1N60P	I <sub>FSM</sub>	500	mA
Forward continuous current	T <sub>amb</sub> = 25 °C	1N60	I <sub>F</sub>	30	mA
		1N60P	I <sub>F</sub>	50	mA

**Thermal Characteristics** Tamb =25 °C unless otherwise specified

Parameter	Test Condition	Symbol	Value	Unit
Thermal resistance, Junction to ambient	I = 4 mm, T <sub>L</sub> = constant	R <sub>thJA</sub>	350	°C / W
Junction temperature		T <sub>j</sub>	125	°C
Storage temperature		T <sub>stg</sub>	- 65 ~ 125	°C

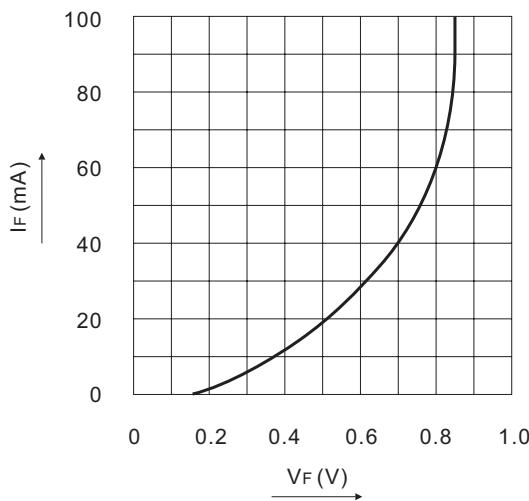
**Electrical Characteristics** Tamb =25 °C unless otherwise specified

Parameter	Test Condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	I <sub>F</sub> = 1 mA	1N60	V <sub>F</sub>	—	0.32	0.5	V
		1N60P	V <sub>F</sub>	—	0.24	0.5	V
	I <sub>F</sub> = 30 mA	1N60	V <sub>F</sub>	—	0.65	1.0	V
Reverse leakage current	V <sub>R</sub> = 15 V	1N60P	V <sub>F</sub>	—	0.65	1.0	V
		1N60	I <sub>R</sub>	—	0.1	0.5	µA
Diode capacitance	V <sub>R</sub> = 1V, f = 1MHz	1N60	C <sub>tot</sub>	—	2.0	—	pF
	V <sub>R</sub> = 10V, f = 1MHz	1N60P	C <sub>tot</sub>	—	6.0	—	pF
Detection efficiency (See the measurement circuit)	V <sub>IN</sub> = 3 V, f = 30 MHz C <sub>L</sub> = 10pF, R <sub>L</sub> = 3.8kΩ		η	—	0.60	—	—
Reverse recovery time	I <sub>F</sub> = 10mA, I <sub>R</sub> = 10mA, I <sub>rr</sub> = 1m, R <sub>L</sub> = 100 Ω		trr	—	—	1	ns

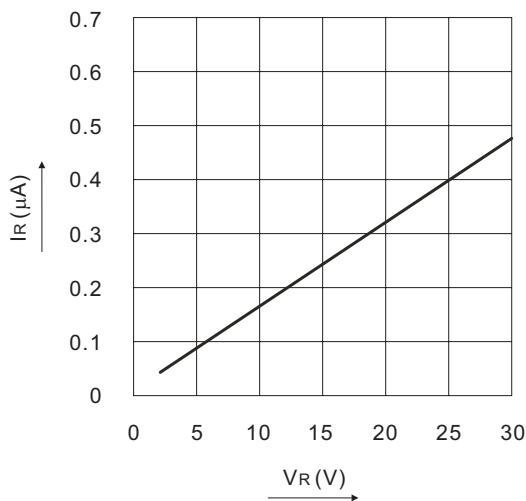
**Detection Efficiency Measurement Circuit**

**1N60 Ratings and Characteristic Curves** Tamb = 25 °C unless otherwise specified

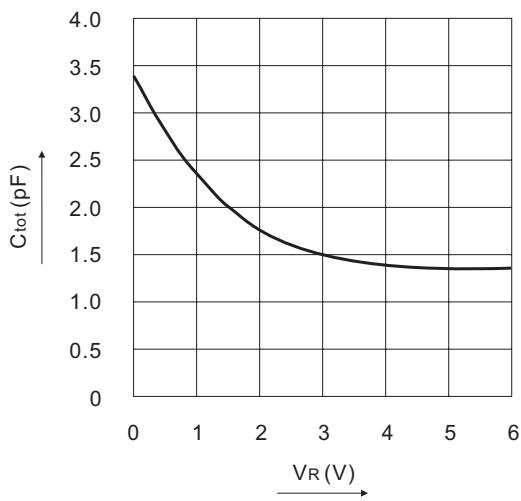
Forward current versus forward voltage (typical values)



Reverse current versus continuous reverse voltage

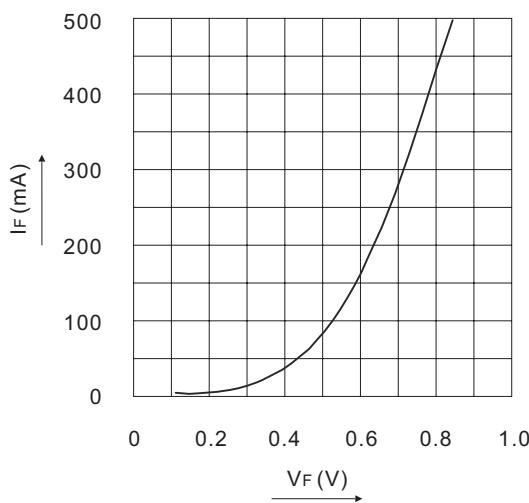


Diode capacitance versus continuous reverse voltage

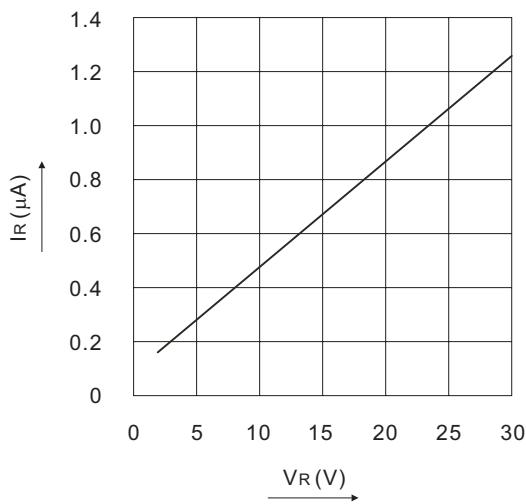


**1N60P Ratings and Characteristic Curves** Tamb = 25 °C unless otherwise specified

Forward current versus forward voltage (typical values)



Reverse current versus continuous reverse voltage



Diode capacitance versus continuous reverse voltage

